

# ZXTN5551FL 160V, SOT23, NPN High voltage transistor

## Summary

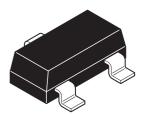
**BV<sub>CEO</sub> > 160V** 

 $BV_{EBO} > 6V$ 

 $I_{C(cont)} = 600 mA$ 

 $P_{D} = 330 \text{mW}$ 

Complementary part number ZXTP5401FL

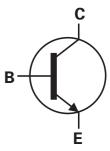


## **Description**

A high voltage NPN transistor in a small outline surface mount package.

## **Features**

- 160V rating
- SOT23 package

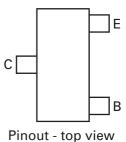


## **Applications**

· High voltage amplification

## **Ordering information**

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN5551FLTA	7	8	3000



**Device marking** 

N51

# **Absolute maximum ratings**

Parameter	Symbol	Limit	Unit
Collector-base voltage	V <sub>CBO</sub>	180	V
Collector-emitter voltage	V <sub>CEO</sub>	160	V
Emitter-base voltage	V <sub>EBO</sub>	6	V
Continuous collector current <sup>(a)</sup>	I <sub>C</sub>	600	mA
Power dissipation at T <sub>amb</sub> =25°C <sup>(a)</sup>	P <sub>D</sub>	330	mW
Linear derating factor		2.64	mW/°C
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	°C

## Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	379	°C/W

### NOTES:

(a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

# Electrical characteristics (at T<sub>amb</sub> = 25°C unless otherwise stated)

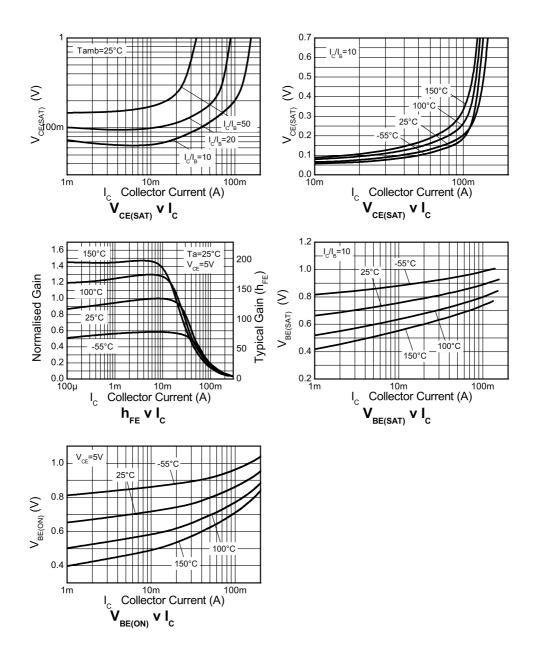
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CBO</sub>	180	270		V	I <sub>C</sub> = 100μA
Collector-emitter breakdown voltage (base open)	BV <sub>CEO</sub>	160	200		V	I <sub>C</sub> = 1mA <sup>(*)</sup>
Emitter-base breakdown voltage	BV <sub>EBO</sub>	6	7.85		V	$I_E = 10\mu A$
Collector cut-off current	I <sub>CBO</sub>		<1	50	nA	V <sub>CB</sub> = 120V
				50	μΑ	$V_{CB} = 120V, T_{amb} = 100^{\circ}C$
Collector-emitter saturation	V <sub>CE(sat)</sub>		65	150	V	$I_C = 10 \text{mA}, I_B = 1 \text{mA}^{(*)}$
voltage			115	200	V	$I_C = 50 \text{mA}, I_B = 5 \text{mA}^{(*)}$
Base-emitter saturation	V <sub>BE(sat)</sub>		760	1000	mV	$I_C = 10mA, I_B = 1mA^{(*)}$
voltage			840	1200	mV	$I_C = 50 \text{mA}, I_B = 5 \text{mA}^{(*)}$
Static forward current	h <sub>FE</sub>	80	135			$I_C = 1mA, V_{CE} = 5V^{(*)}$
transfer ratio		80	145	250		$I_C = 10 \text{mA}, V_{CE} = 5 V^{(*)}$
		30	65			$I_C = 50 \text{mA}, V_{CE} = 5 V^{(*)}$
Transition frequency	f <sub>T</sub>		130		MHz	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 10V, f = 100MHz
Output capacitance	C <sub>OBO</sub>			6	pF	V <sub>CB</sub> = 10V, f = 1MHz <sup>(*)</sup>
Small signal	h <sub>FE</sub>	50		260		$I_C = 10 \text{mA}, V_{CE} = 10 \text{V},$ $f = 1 \text{kHz}^{(\dagger)}$
Delay time	t <sub>(d)</sub>		95		ns	$V_{CC} = 10V, I_C = 10mA, I_{B1} =$
Rise time	t <sub>(r)</sub>		64		ns	I <sub>B2</sub> = 1mA
Storage time	t <sub>(s)</sub>		1256		ns	
Fall time	t <sub>(f)</sub>		140		ns	

### NOTES:

<sup>(\*)</sup> Measured under pulsed conditions. Pulse width  ${\leq}300\mu s;$  duty cycle  ${\leq}2\%.$ 

<sup>(†)</sup> Periodic sample test only

# **Typical characteristics**



# ZXTN5551FL

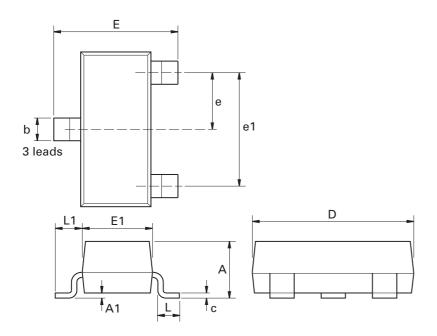
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# Package outline - SOT23



Dim.	Millin	neters	Inc	hes	Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
Α	-	1.12	-	0.044	e1	1.90	NOM	0.075	NOM
A1	0.01	0.10	0.0004	0.004	Е	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
С	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95	NOM	0.037	NOM	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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